

Appl. No. 10/765,808  
Amdt. Dated 03/19/2009  
Response to Office Action of 11/24/2008

Attorney Docket No.: N1085-00256  
[TSMC2003-0899]

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application:

- 1 1. (Currently Amended) A plasma etching apparatus comprising a chuck adapted to  
2 retain ~~for retaining~~ a substrate thereover and hardware that is formed of a material that  
3 includes oxygen impregnated therein such that said oxygen is released when an etching  
4 operation is carried out, wherein said hardware comprises a focus ring and at least a  
5 portion of said focus ring substantially continuously extends directly underneath a  
6 peripheral portion of said chuck.
- 1 2. (Previously Presented). The plasma etching apparatus as in claim 1, wherein  
2 said chuck is substantially circular and said focus ring peripherally surrounds said  
3 chuck.
- 1 3. (Currently Amended) The plasma etching apparatus as in claim [[8]] 2, wherein  
2 said focus ring comprises a lower focus ring and further comprising an upper focus ring.  
3 at least a portion of said lower focus ring substantially continuously extending ~~extends~~  
4 below a peripheral portion of said chuck.
- 1 4. (Original) The plasma etching apparatus as in claim 1, wherein said chuck  
2 comprises an electrostatic chuck.
- 1 5. (Original) The plasma etching apparatus as in claim 1, wherein said hardware  
2 comprises a focus ring composed primarily of quartz.
- 1 6. (Original) The plasma etching apparatus as in claim 1, wherein said hardware  
2 comprises a focus ring formed of a ceramic.

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1 7. (Previously Presented) The plasma etching apparatus as in claim 1, further  
2 comprising a further focus ring, said focus ring and said further focus ring forming a  
3 focus ring set that peripherally surrounds said chuck.

1 8. (Cancelled).

1 9. (Previously Presented) The plasma etching apparatus as in claim 1, further  
2 comprising said focus ring maintainable at a temperature no greater than a temperature  
3 of said substrate while an etching operation is carried out upon said substrate.

1 10. (Original) The plasma etching apparatus as in claim 9, wherein said chuck  
2 comprises an electrostatic chuck and said substrate comprises a semiconductor  
3 substrate.

1 11. (Currently Amended) The plasma etching apparatus as in claim 9, wherein said  
2 chuck comprises an electrostatic chuck and said focus ring maintains contact with said  
3 electrostatic chuck and said electrostatic chuck is cooled during said etching operation.

1 12. (Currently Amended) The plasma etching apparatus as in claim 11, wherein said  
2 focus ring is disposed peripherally around said substrate and includes a portion that  
3 rests on an annular landing section of said electrostatic chuck.

1 13-28. (Cancelled)

1 29. (Currently Amended) A plasma etching apparatus comprising a chuck adapted to  
2 retain ~~for retaining~~ a substrate thereover and a focus ring peripherally surrounding said  
3 chuck and formed of a focus ring material that includes oxygen throughout the focus  
4 ring material, such that said oxygen is released when an etching operation is carried  
5 out, wherein at least a portion of said focus ring substantially continuously extends  
6 directly underneath a peripheral portion of said chuck.

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1 30. (Previously Presented) The plasma etching apparatus as in claim 29, further  
2 comprising said chuck formed of an oxygen-impregnated material.

1 31. (Previously Presented) The plasma etching apparatus as in claim 30, wherein  
2 said chuck comprises an electrostatic chuck.

1 32. (Previously Presented) The plasma etching apparatus as in claim 31, wherein  
2 said chuck is disposed within an etching chamber and further comprising said etching  
3 chamber containing therein further hardware formed of said oxygen-impregnated  
4 material.

1 33. (Cancelled)